Michael M Oye

List of Publications by Year in descending order

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MICHAEL MOVE

#	Article	IF	CITATIONS
1	Design and synthesis of a near infra-red luminescent hexanuclear Zn–Nd prism. Chemical Communications, 2006, , 1836-1838.	4.1	142
2	Multinuclear Luminescent Schiff-Base Znâ^'Nd Sandwich Complexes. Inorganic Chemistry, 2006, 45, 4340-4345.	4.0	139
3	Synthesis and near infrared luminescence of a tetrametallic Zn2Yb2 architecture from a trinuclear Zn3L2 Schiff base complex. Dalton Transactions, 2005, , 849.	3.3	95
4	Synthesis, crystal structures and antenna-like sensitization of visible and near infrared emission in heterobimetallic Zn–Eu and Zn–Nd Schiff base compounds. Polyhedron, 2006, 25, 271-278.	2.2	78
5	Vertical ZnO nanowire growth on metal substrates. Nanotechnology, 2012, 23, 194015.	2.6	66
6	Near Infrared Luminescence and Supramolecular Structure of a Helical Triple-Decker Yb(III) Schiff Base Cluster. Crystal Growth and Design, 2006, 6, 2122-2125.	3.0	50
7	Transformation of a Luminescent Benzimidazole-Based Yb3 Cluster into a One-Dimensional Coordination Polymer. Crystal Growth and Design, 2010, 10, 970-976.	3.0	26
8	Influence of metal–ligand ratio on benzimidazole based luminescent lanthanide complexes: 3-D network structures and chloride anion binding. New Journal of Chemistry, 2011, 35, 310-318.	2.8	26
9	Vertical graphene by plasma-enhanced chemical vapor deposition: Correlation of plasma conditions and growth characteristics. Journal of Materials Research, 2014, 29, 417-425.	2.6	23
10	Supramolecular assembly of nanometer-sized heterobimetallic 3d–4f complexes formed with benzimidazole based N,O-donor ligands. Polyhedron, 2006, 25, 881-887.	2.2	22
11	Effects of different plasma species (atomic N, metastable N2*, and ions) on the optical properties of dilute nitride materials grown by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2007, 91, .	3.3	14
12	Controlled growth of vertical ZnO nanowires on copper substrate. Applied Physics Letters, 2013, 102, .	3.3	14
13	Diffusion mechanisms of indium and nitrogen during the annealing of InGaAs quantum wells with GaNAs barriers and GaAs spacer layers. Applied Physics Letters, 2005, 86, 151903.	3.3	12
14	Resistive switching in single vertically-aligned ZnO nanowire grown directly on Cu substrate. Chemical Physics Letters, 2013, 575, 112-114.	2.6	12
15	Time and temperature dependence on rapid thermal annealing of molecular beam epitaxy grown Ga0.8In0.2N0.01As0.99 quantum wells analyzed using photoluminescence. Journal of Electronic Materials, 2003, 32, 29-33.	2.2	10
16	Ion damage effects from negative deflector plate voltages during the plasma-assisted molecular-beam epitaxy growth of dilute nitrides. Applied Physics Letters, 2005, 86, 221902.	3.3	9
17	Rapid thermal annealing effects on the photoluminescence properties of molecular beam epitaxy-grown Galn(N)As quantum wells with Ga(N)As spacers and barriers. Journal of Electronic Materials, 2004, 33, 851-860.	2.2	8
18	Construction of a variable aperture cell for source flux control in a molecular-beam epitaxy environment. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2004, 22, 735.	2.1	3

#	Article	IF	CITATIONS
19	Critical RF damage conditions for the plasma-assisted molecular beam epitaxy growth of GaInNAs with dilute N2/Ar gas mix. Journal of Crystal Growth, 2005, 280, 7-15.	1.5	3
20	Role of ion damage on unintentional Ca incorporation during the plasma-assisted molecular-beam epitaxy growth of dilute nitrides using N[sub 2]â^•Ar source gas mixtures. Journal of Vacuum Science & Technology B, 2008, 26, 1058.	1.3	2